

2SK2144

Silicon N Channel MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC – DC converter

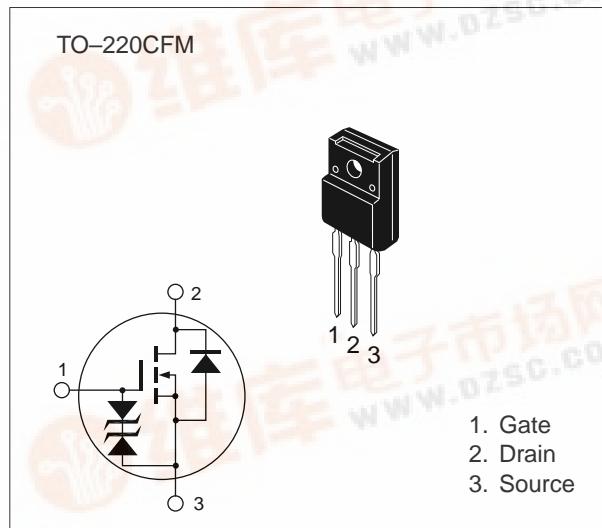


Table 1 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	600	V
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	3	A
Drain peak current	$I_{D(\text{pulse})}^*$	6	A
Body-drain diode reverse drain current	I_{DR}	3	A
Channel dissipation	P_{ch}^{**}	25	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* PW ≤ 10 μs , duty cycle ≤ 1 %

** Value at $T_c = 25^\circ\text{C}$

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	600	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR)GSS}	±30	—	—	V	I _G = ±100 µA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	µA	V _{GS} = ±25 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	250	µA	V _{DS} = 500 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	3.0	V	I _D = 1 mA, V _{DS} = 10 V
Static drain to source on state resistance	R _{DS(on)}	—	3.8	5.0	Ω	I _D = 1 A V _{GS} = 10 V *
Forward transfer admittance	y _{fsl}	1.2	2.0	—	S	I _D = 1 A V _{DS} = 10 V *
Input capacitance	C _{iss}	—	295	—	pF	V _{DS} = 10 V
Output capacitance	C _{oss}	—	70	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	12	—	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	—	8	—	ns	I _D = 1 A
Rise time	t _r	—	25	—	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	—	65	—	ns	R _L = 30Ω
Fall time	t _f	—	30	—	ns	
Body-drain diode forward voltage	V _{DF}	—	0.9	—	V	I _F = 2 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	—	220	—	ns	I _F = 2 A, V _{GS} = 0, diF / dt = 100 A / µs

* Pulse Test

■ See characteristic curve of 2SK1572.

